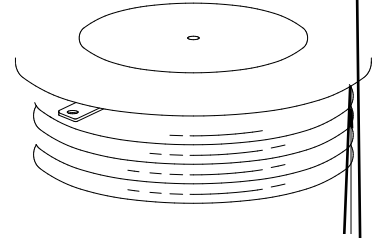


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T8C



Device Type	$V_{RRM}$ (1)	$V_{DRM}$ (1)	$V_{RSM}$ (1)
KP1300/20	2000	2000	2200
KP1300/22	2200	2200	2400
KP1300/24	2400	2400	2500

$V_{RRM}$  = Repetitive peak reverse voltage  
 $V_{DRM}$  = Repetitive peak off state voltage  
 $V_{RSM}$  = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	$I_{RRM}/I_{DRM}$	5 mA 65 mA (3)
Critical rate of voltage rise	$dv/dt$ (4)	1000 V/ s



Peak gate power dissipation	$P_{GM}$		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	$I_{GT}$		200		mA	$V_D = 12\text{ V}; R_L = 3\text{ ohms}; T_j = +25\text{ }^\circ\text{C}$
Gate- trigger voltage	$V_{GT}$	0.7	3.0		V	$V_D = 12\text{ V}; R_L = 3\text{ ohms}; T_j = +25\text{ }^\circ\text{C}$
Peak negative voltage	$V_{GRM}$		5		V	

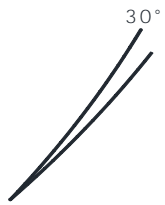
Delay time	$t_d$		3.0	2.5	s	$I_{TM} = 100\text{A}; V_D = 67\%V_{DRM}$ Gate pulse: $V_G = 30\text{V}; R_G = 10\text{ohms};$ $t_r = 0.1\text{ s}; t_p = 20\text{ s}$
Turn-off time (with $V_R = -5\text{ V}$ )	$t_q$			250	s	$I_{TM} = 1000\text{A}; di/dt = -10\text{A/ s};$ $V_R = 100\text{V}; dv/dt = 30\text{V/ s};$ $V_D = 67\%V_{DRM}; T_j = 125$
Reverse recovery charge	$Q_{rr}$				C	$I_{TM} = 1000\text{A } di/dt = -10\text{A/ s};$ $V_R = 100\text{V}; T_j = 125$



Operating temperature	$T_j$	-40	+125		$^\circ\text{C}$	
Storage temperature	$T_{stg}$	-40	+140		$^\circ\text{C}$	
Thermal resistance - junction to case	$R_{(j-c)}$		0.022		$^\circ\text{C/W}$	Double sided cooled
Thermal resistance - case to heatsink	$R_{(c-s)}$		0.005		$^\circ\text{C/W}$	Double sided cooled
Mounting force		23	27	25	kN	
Weight	m			0.46	kg	

\* Mounting surfaces smooth, flat and greased

Max. power dissipation Vs. mean on-state current



Mean forward current, amperes  
Fig 3

